



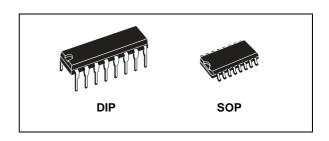
# **DIFFERENT 4-CHANNEL** ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR  $V_{DD} - V_{EE} = 15V$
- HIGH "OFF" RESISTANCE: CHANNEL LEAKAGE  $\pm$  100pA (Typ.) at  $V_{DD}$  -  $V_{EE}$  = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY: < 0.5% DISTORTION TYP. at  $f_{IS} = 1$ KHz,  $V_{IS} = 5$   $V_{pp}$ ,  $V_{DD} - V_{SS} \ge 10V$ , RL =  $10K\Omega$
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2 μW (Typ.) at  $V_{DD}$  -  $V_{SS} = V_{DD}$  -  $V_{EE} = 10V$
- MATCHED SWITCH CHARACTERISTICS:  $R_{ON} = 5\Omega$  (Typ.) FOR  $V_{DD} - V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS: DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT  $I_{I} = 100 \text{nA} \text{ (MAX) AT V}_{DD} = 18 \text{V T}_{A} = 25 ^{\circ}\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS **DEVICES**"

#### DESCRIPTION

The HCF4052B is a monolithic integrated circuit

# fabricated in Metal Oxide Semiconductor

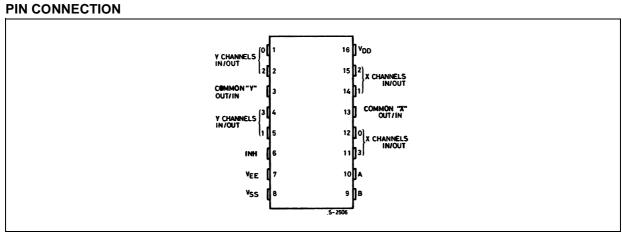


#### ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4052BEY	
SOP	HCF4052BM1	HCF4052M013TR

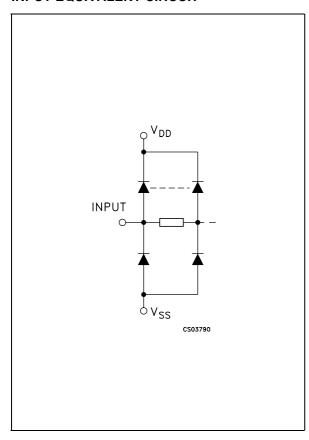
technology available in DIP and SOP packages. The HCF4052B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full  $V_{DD}$  -  $V_{SS}$  and  $V_{DD}$  -V<sub>FF</sub> supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a differential 4-channel multiplexer having two binary control inputs, A and B and an inhibit input. The two binary input signals selects 1 of 4 pairs of channels to be turned on and connect the analog inputs to the outputs.



October 2002 1/11

# **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

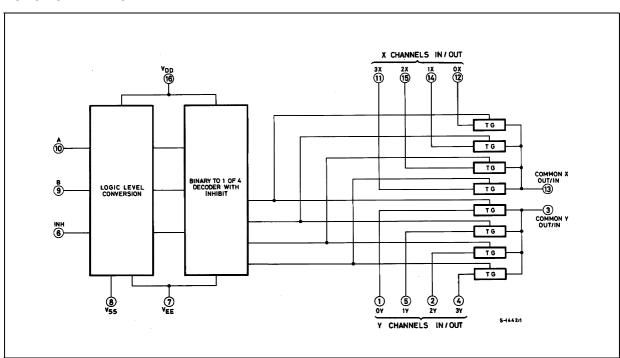
PIN No	SYMBOL	NAME AND FUNCTION
10, 9	A, B	Binary Control Inputs
6	INH	Inhibit Inputs
12, 14, 15, 11	0X to 3X CHANNEL IN/OUT	X channels Input/Output
1, 5, 2, 4	0Y to 3Y CHANNEL IN/OUT	Y channels Input/Output
3	COM Y OUT/ IN	Y Common Output/Input
13	COM X OUT/ IN	X Common Output/Input
7	V <sub>EE</sub>	Supply Voltage
8	$V_{SS}$	Negative Supply Voltage
16	$V_{DD}$	Positive Supply Voltage

# TRUTH TABLE

INHIBIT	В	Α	
0	0	0	0x, 0y
0	0	1	1x, 1y
0	1	0	2x, 2y
0	1	1	3x, 3y
1	Х	Х	NONE

X : Don't Care

# **FUNCTIONAL DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
l <sub>l</sub>	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V<sub>SS</sub> pin voltage.

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

# **DC SPECIFICATIONS**

		Test Condition				Value							
Symbol	Parameter	V <sub>IS</sub>	V <sub>EE</sub>	V <sub>SS</sub>	V <sub>DD</sub>	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
	ownorios or r j				20		0.08	100		3000		3000	
SWITCH													
R <sub>ON</sub>	Resistance	0 <u>&lt;</u> V <sub>1</sub> <u>&lt;</u>			5		470	1050		1200		1200	
		V <sub>DD</sub>	0	0	10		180	400		520		520	Ω
		. 00			15		125	280		360		360	
$\Delta_{ON}$	Resistance $\Delta_{RON}$	0 <u>&lt;</u> V <sub>1</sub> ≤			5		10						
	(between any 2 of	V <sub>DD</sub>	0	0	10		10						Ω
	4 switches)	- 00			15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
C <sub>I</sub>	Input Capacitance						5						
C <sub>O</sub>	Output Capacitance		-5	-5	5		18						pF
C <sub>IO</sub>	Feed through						0.2						
CONTRO	DL (Address or Inhi	bit)		ı	I			I	I				I
V <sub>IL</sub>	Input Low Voltage		V <sub>EE</sub> =	= Voc	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD	to \		15			4		4		4	
V <sub>IH</sub>	Input High Voltage	thru 1KΩ		2μΑ	5	3.5			3.5		3.5		
			(on al	I OFF	10	7			7		7		V
			chan	nels)	15	11			11		11		
I <sub>IH,</sub> I <sub>IL</sub>	Input Leakage Current	VI	= 0/18\	/	18		±10 <sup>-3</sup>	±0.1		±1		±1	μΑ
C <sub>I</sub>	Input Capacitance						5	7.5					рF

<sup>\*</sup> Determined by minimum feasible leakage measurement for automating testing.

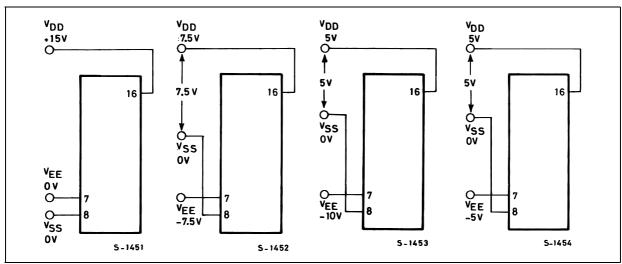
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}C$ ,  $C_{L} = 50 pF$ , all input square wave rise and fall time = 20 ns )

				Test Co	ndition			Value				
Parameter	V <sub>EE</sub> (V)	<b>R</b> <sub>L</sub> (ΚΩ)	f <sub>I</sub> (KHz)	<b>V</b> <sub>I</sub> (V)	<b>V</b> <sub>SS</sub> (V)	<b>V</b> <sub>DD</sub> (V)		Min.	Тур.	Max.		
Propagation Delay				$V_{DD}$		5			30	60		
Time (signal input to		200		V DD		10			15	30	ns	
output)						15			11	20		
Frequency Response Channel "ON" (sine	= V <sub>SS</sub>	1		5(*)		10	V <sub>O</sub> at Common OUT/IN		25		MHz	
wave input) at $20 \log V_O/V_I = -3dB$	- VSS	•		3( )		10	V <sub>O</sub> at any channel		60		IVII IZ	
Feed through (all channels OFF) at	= V <sub>SS</sub>	1		5(*)		10	V <sub>O</sub> at Common OUT/IN		10		MHz	
$20 \log V_O/V_I = -40 dB$	50	,		3( )		10	V <sub>O</sub> at any channel		8		IVII IZ	
Frequency Signal Crosstalk at	= V <sub>SS</sub>	1		5(*)		10	Between Sections (measured on common)		6		MHz	
20 log V <sub>O</sub> /V <sub>I</sub> = -40dB	- \$55	'		3( )		10	Between Sections (measured on any channel)		10		IVII IZ	
Sine Wave Distortion				2(*)		5			0.3			
f <sub>IS</sub> = 1KHz Sine Wave	$=V_{SS}$	10	1	3(*)		10			0.2		%	
152				5(*)		15			0.12			
CONTROL (Address	or Inhibi	t)										
Propagation Delay:	0				0	5			360	720		
Address to Signal OUT (Channels ON	0				0	10			160	320	ns	
or OFF)	0				0	15			120	240	113	
,	-5				0	5			225	450		
Propagation Delay:	0				0	5			360	720		
Inhibit to Signal OUT (Channel turning ON)	0	1			0	10			160	320	ns	
(Chainer turning ON)	0	·			0	15			120	240		
	-10				0	5			200	400		
Propagation Delay:	0					5	_		200	450		
Inhibit to Signal OUT (Channel turning	0	10				10			90	210	ns	
OFF)	0	10				15	]		70	160	113	
J. 1 /	-10					5			130	300		
Address or Inhibit to Signal Crosstalk	0	10 <sup>(1)</sup>			0	10	$V_C = V_{DD} - V_{SS}$ (square wave)		65		mV peak	

<sup>(1)</sup> Both ends of channel.

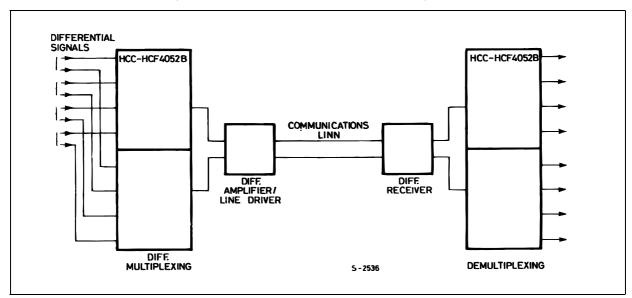
\* Peak to Peak voltage symmetrical about (V<sub>DD</sub> - V<sub>EE</sub> ) /2

#### **TYPICAL BIAS VOLTAGES**



The ADDRESS (digtal-control inputs) and INHIBIT logic levels are : "0"= $V_{SS}$  and "1"= $V_{DD}$ . The analog signal (through the TG) may swing from  $V_{EE}$  to  $V_{DD}$ 

#### TYPICAL APPLICATIONS (TYPICAL TIME-DIVISION APPLICATION)

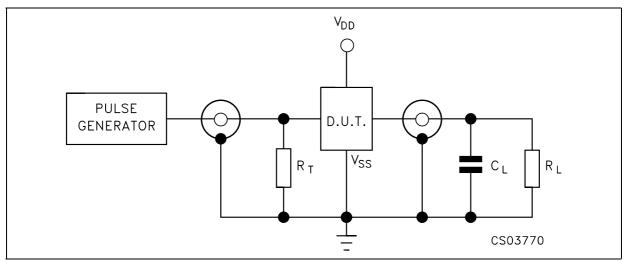


# **SPECIAL CONSIDERATIONS**

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if  $V_{DD}$  -  $V_{SS}$  = 3V, a  $V_{DD}$  -  $V_{EE}$  of up to 13V can be controlled; for  $V_{DD}$  -  $V_{EE}$  level differences above 13V, a  $V_{DD}$  -  $V_{SS}$  of at least 4.5V is required. For example, if  $V_{DD}$  = +5,  $V_{SS}$  = 0, and  $V_{EE}$  = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In certain applications, the external load resistor

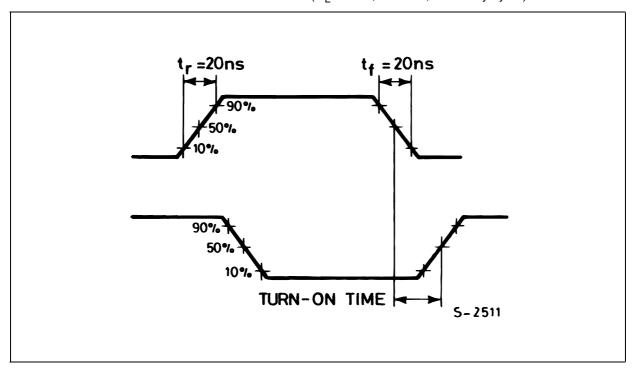
current may include both  $V_{DD}$  and signal-line components. To avoid drawing  $V_{DD}$  current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from  $R_{ON}$  values shown in DC SPECIFICATIONS). No  $V_{DD}$  current will flow through  $R_{L}$  if the switch current flows into leads 3 and 13.

#### **TEST CIRCUIT**

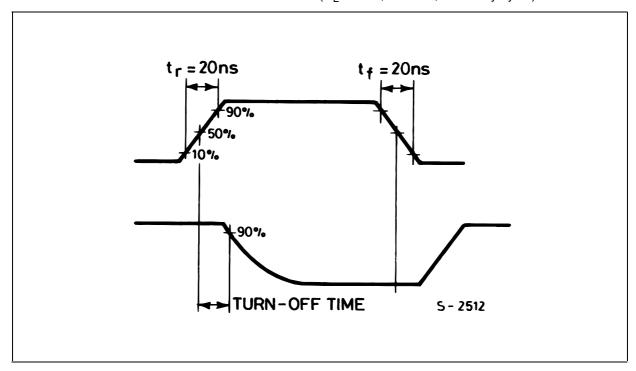


 $C_L$  = 50pF or equivalent (includes jig and probe capacitance)  $R_L$  = 200KΩ  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50Ω)

# **WAVEFORM 1 : CHANNEL BEING TURNED ON** ( $R_L = 1 \text{K}\Omega$ , f=1MHz; 50% duty cycle)

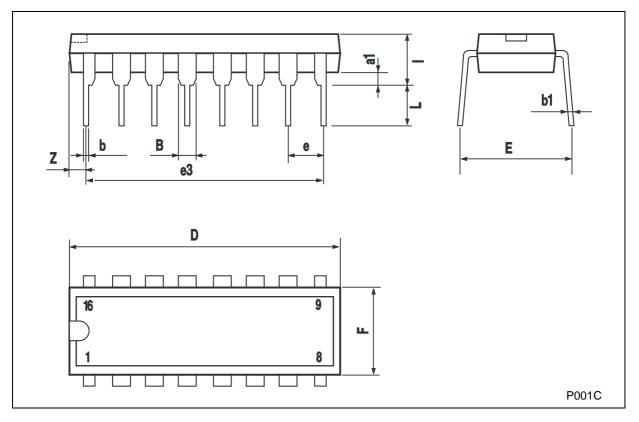


# **WAVEFORM 2 : CHANNEL BEING TURNED OFF** ( $R_L$ = 1K $\Omega$ , f=1MHz; 50% duty cycle)



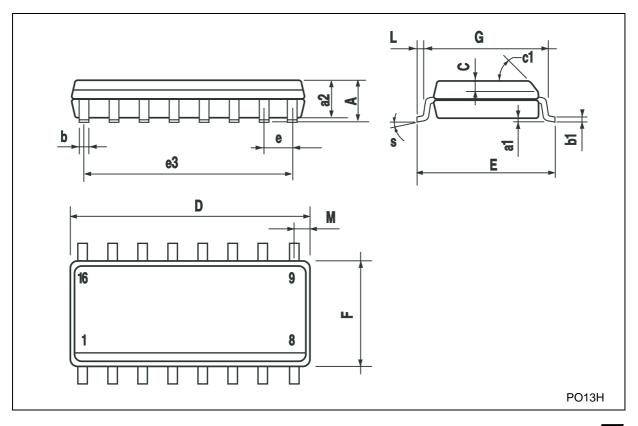
# Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



# **SO-16 MECHANICAL DATA**

DIM.		mm.		inch				
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (ı	max.)	ı	1		



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